

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	0	epitax\$4 with (gallium or aluminum or indium or Ga or Al or In) with nitride with (CVD or MOCVD) with (hydride adj vapor adj phase adj deposit\$3)	USPAT ; EPO; JPO; DERW ENT; IBM_T DB	2003/05/07 12:50
2	BRS	L2	0	epitax\$4 with (gallium or aluminum or indium or Ga or Al or In) with nitride with ((hydride adj vapor adj phase adj deposit\$3) or HVPD)	USPAT ; EPO; JPO; DERW ENT; IBM_T DB	2003/05/07 12:52
3	BRS	L4	1	epitax\$4 same (gallium or aluminum or indium or Ga or Al or In) same nitride same ((hydride adj vapor adj phase adj deposit\$3) or HVPD or HVPR)	USPAT ; EPO; JPO; DERW ENT; IBM_T DB	2003/05/07 12:57
4	BRS	L3	1	epitax\$4 same (gallium or aluminum or indium or Ga or Al or In) same nitride same ((hydride adj vapor adj phase adj deposit\$3) or HVPD)	USPAT ; EPO; JPO; DERW ENT; IBM_T DB	2003/05/07 12:56
5	BRS	L5	56	epitax\$4 same (gallium or aluminum or indium or Ga or Al or In) same nitride same ((hydride adj vapor adj phase) or HVPD or HVPR)	USPAT ; EPO; JPO; DERW ENT; IBM_T DB	2003/05/07 12:58
6	BRS	L6	4	5 and (buffer with nitride with (MOCVD or CVD))	USPAT ; EPO; JPO; DERW ENT; IBM_T DB	2003/05/07 12:59